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Complete if Known

Application Number	08/903486
Filing Date	July 29, 1997
First Named Inventor	Forbes, Leonard
Group Art Unit	2811
Examiner Name	Kang, Donghee

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Sheet 1 of 3

Attorney Docket No: 303.326US1 Technology Center 2100

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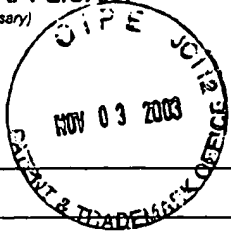
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Examiner Name	Kang, Donghee

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Attorney Docket No: 303.326US1

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-Issue number(s), publisher, city and/or country where published.	T ²
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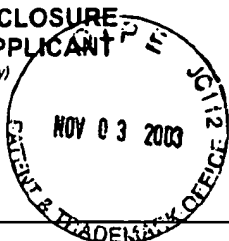
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First Named Inventor	Forbes, Leonard	Technology Center 2100
Group Art Unit	2811	
Examiner Name	Kang, Donghee	

Sheet 3 of 3

Attorney Docket No: 303.326US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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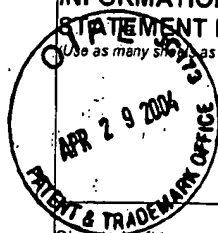
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Application Number	08/903,486
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Group Art Unit	2811
Examiner Name	Kang, Donghee

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